

# TO-92 Plastic-Encapsulate Transistors

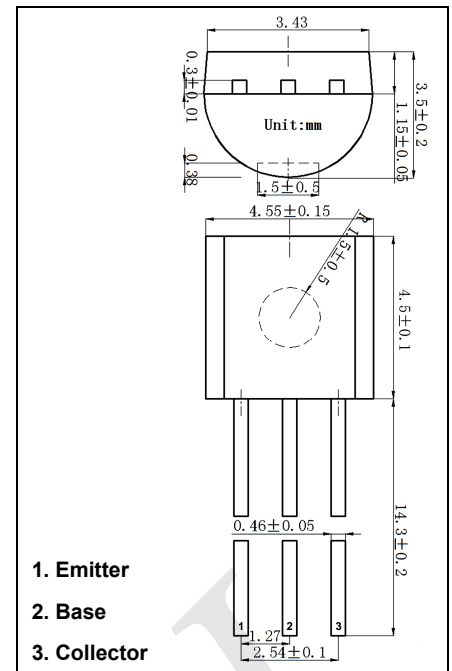
## 2N2907A-338 PNP Transistors

### Features

- Complementary NPN Type available (2N2222A)

### Maximum Ratings (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector Base Voltage	-60	V
V <sub>CEO</sub>	Collector Emitter Voltage	-40	V
V <sub>EBO</sub>	Emitter Base Voltage	-5	V
I <sub>c</sub>	Collector Current	-600	mA
P <sub>D</sub>	Collector Power Dissipation	625	mW
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55 ~ +150	°C
R <sub>θJA</sub>	Thermal Resistance from Junction to Ambient	200	°C/W



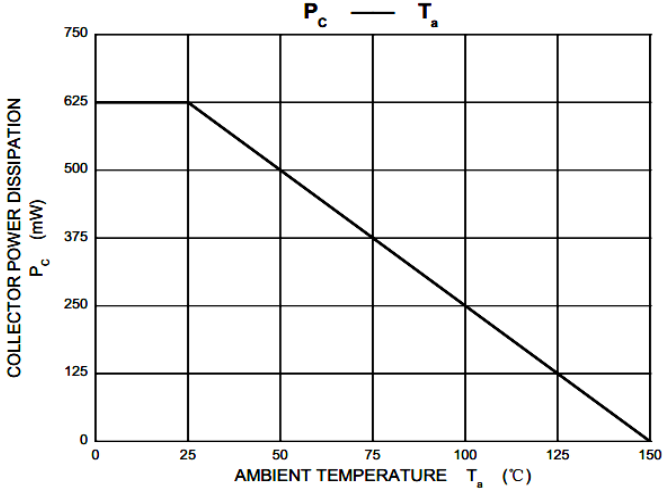
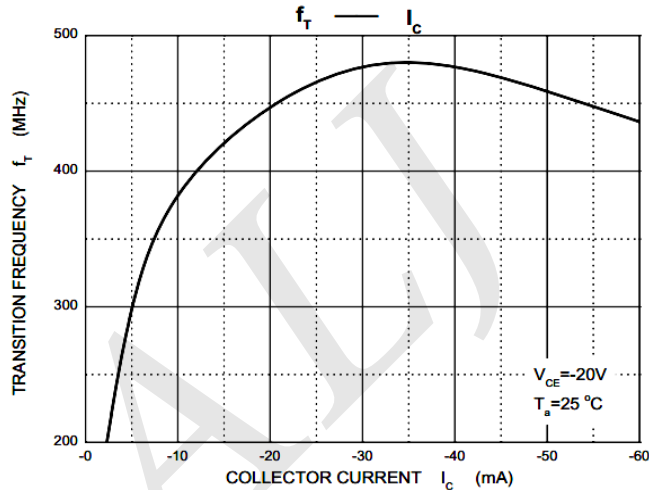
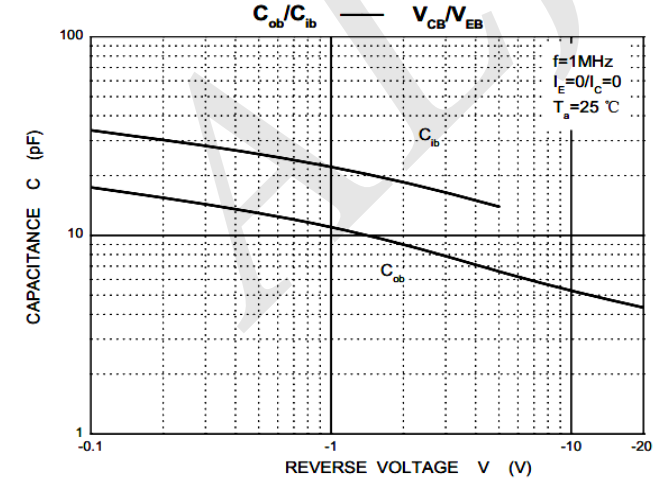
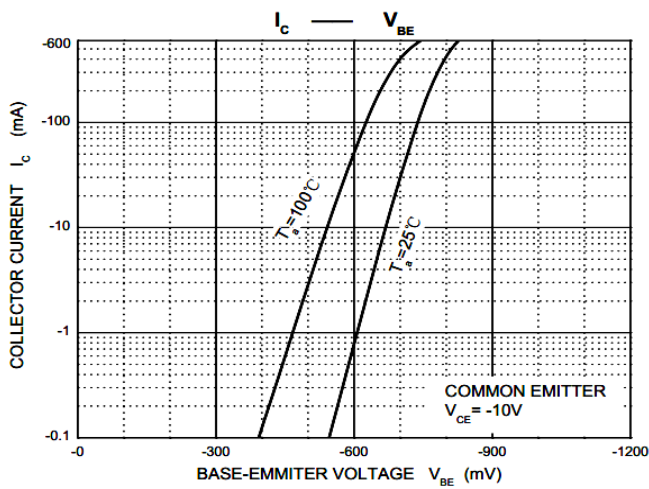
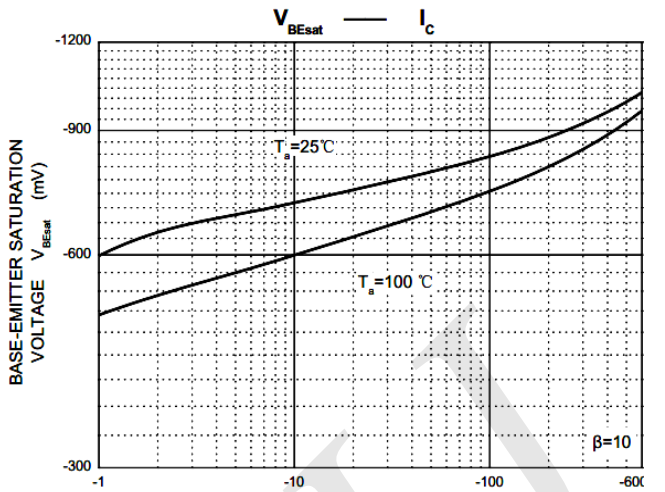
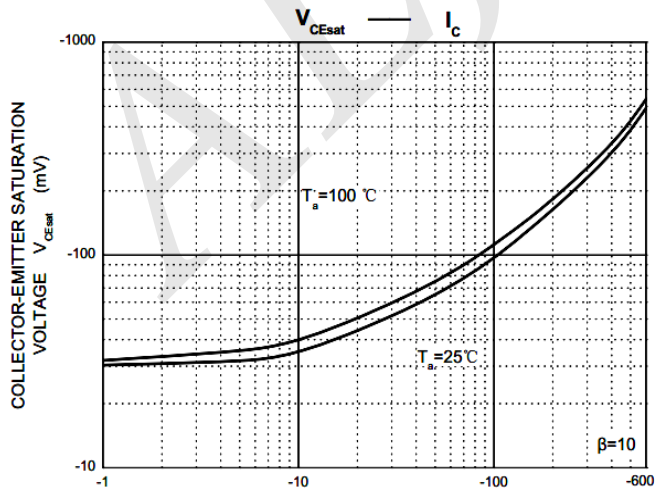
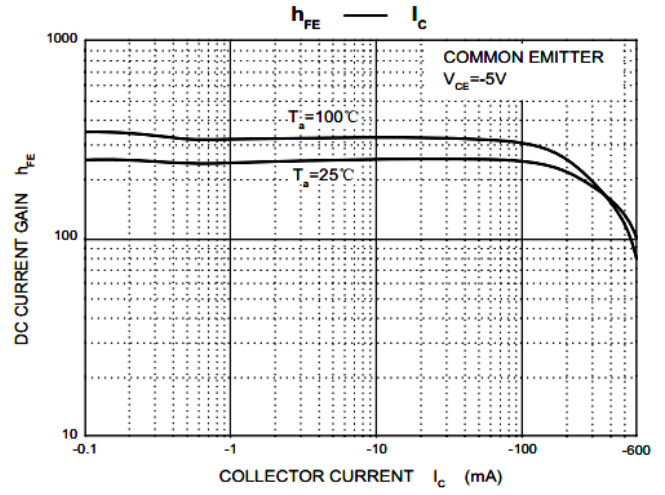
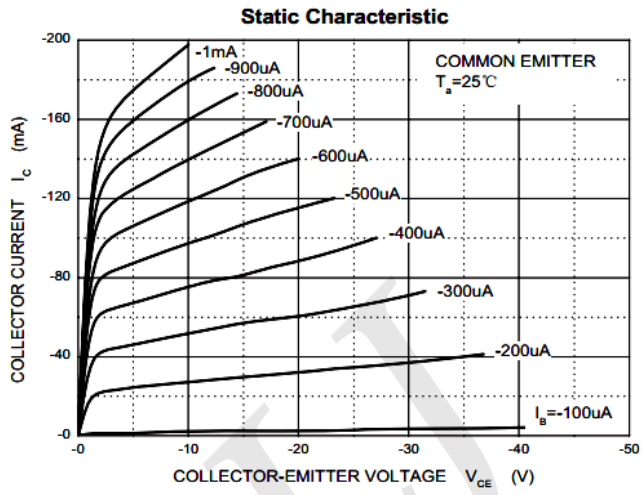
### Electrical Characteristics (T<sub>a</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>c</sub> = -10μA, I <sub>E</sub> = 0	-60			V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>c</sub> = -10mA, I <sub>B</sub> = 0	-40			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> = -10μA, I <sub>c</sub> = 0	-5			V
I <sub>cBO</sub>	Collector cut-off current	V <sub>CB</sub> = -50V, I <sub>E</sub> = 0			-10	nA
I <sub>cEX</sub>	Collector cut-off current	V <sub>CE</sub> = -30V, V <sub>EB(off)</sub> = -0.5V			-50	nA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> = -3V, I <sub>c</sub> = 0			-10	nA
h <sub>FE(1)</sub>	DC current gain	V <sub>CE</sub> = -5V, I <sub>c</sub> = -1mA	100			
h <sub>FE(2)</sub>		V <sub>CE</sub> = -10V, I <sub>c</sub> = -0.1mA	78			
h <sub>FE(3)</sub>		V <sub>CE</sub> = -10V, I <sub>c</sub> = -150mA	100		300	
h <sub>FE(4)</sub>		V <sub>CE</sub> = -10V, I <sub>c</sub> = -500mA	52			
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>c</sub> = -150mA, I <sub>B</sub> = -15mA			-0.4	V
		I <sub>c</sub> = -500mA, I <sub>B</sub> = -50mA			-0.67	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>c</sub> = -150mA, I <sub>B</sub> = -15mA			-1	V
		I <sub>c</sub> = -500mA, I <sub>B</sub> = -50mA			-1.2	V
f <sub>T</sub>	Transition frequency	V <sub>CE</sub> = -20V, I <sub>c</sub> = -50mA, f = 100MHz	200			MHz
t <sub>d</sub>	Delay time	V <sub>CC</sub> = -30V, I <sub>c</sub> = -150mA,			10	ns
t <sub>r</sub>	Rise time	I <sub>B1</sub> = -15mA			25	ns
t <sub>s</sub>	Storage time	V <sub>CC</sub> = -6V, I <sub>c</sub> = -150mA,			225	ns
t <sub>f</sub>	Fall time	I <sub>B1</sub> = -I <sub>B2</sub> = -15mA			60	ns

### Classification OF h<sub>FE(1)</sub>

Rank	L	H
Range	100-200	200-300

# Typical Characteristics



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